



US 20140217415A1

(19) **United States**

(12) **Patent Application Publication**

Kim et al.

(10) **Pub. No.: US 2014/0217415 A1**

(43) **Pub. Date: Aug. 7, 2014**

(54) **THIN FILM TRANSISTOR AND ORGANIC LIGHT-EMITTING DISPLAY**

(30) **Foreign Application Priority Data**

Oct. 1, 2010 (KR) 10-2010-0095958

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Publication Classification

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(51) **Int. Cl.**
H01L 27/12 (2006.01)

(52) **U.S. Cl.**
CPC **H01L 27/1222** (2013.01); **H01L 27/127**
(2013.01)

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USPC **257/72**

(21) Appl. No.: **14/244,584**

(57) **ABSTRACT**

(22) Filed: **Apr. 3, 2014**

A thin film transistor including: a substrate; an active layer formed over the substrate; a gate insulating layer formed over the active layer; a gate electrode formed over the gate insulating layer; an interlayer insulating layer formed over the gate electrode; and source and drain electrodes that contact the active layer via the interlayer insulating layer. The source and drain electrodes may have a structure including an aluminum (Al) layer, an aluminum-nickel alloy (AlNiX) layer, and an indium tin oxide (ITO) layer, which are sequentially stacked.

Related U.S. Application Data

(62) Division of application No. 13/103,938, filed on May 9, 2011, now Pat. No. 8,716,758.

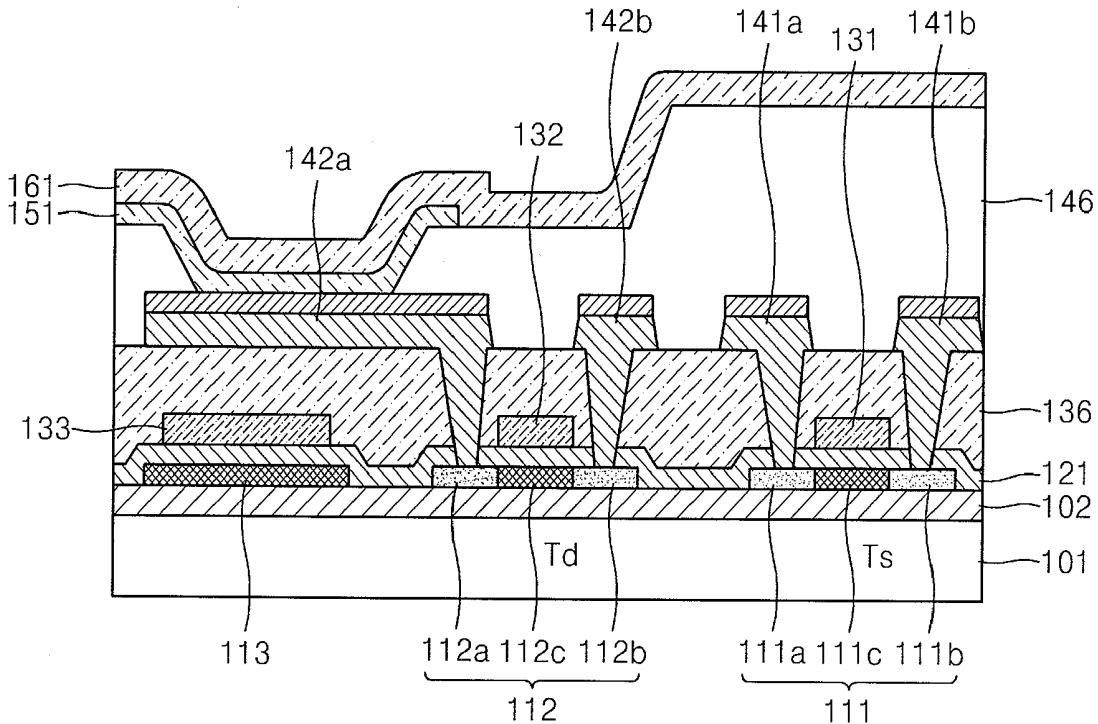


FIG. 1

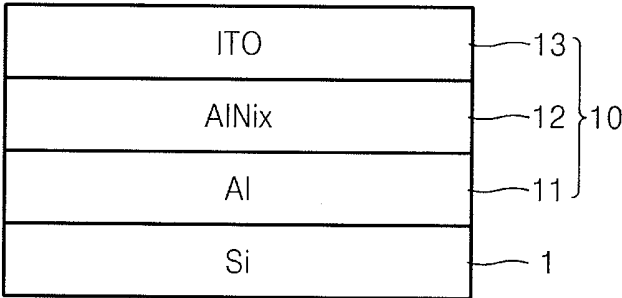


FIG. 2

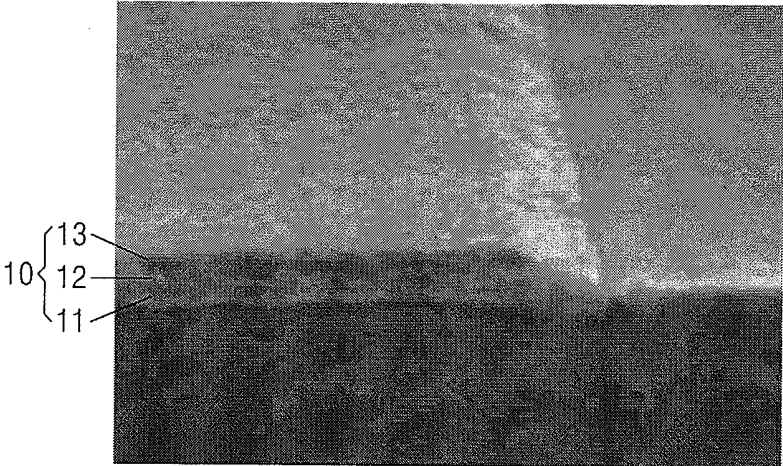


FIG. 3

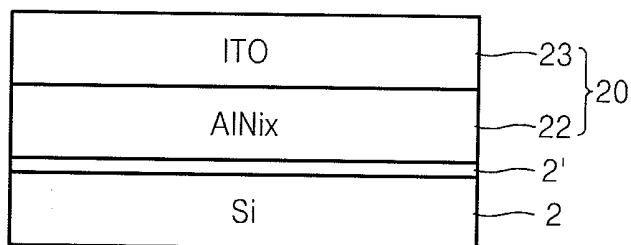


FIG. 4



FIG. 5

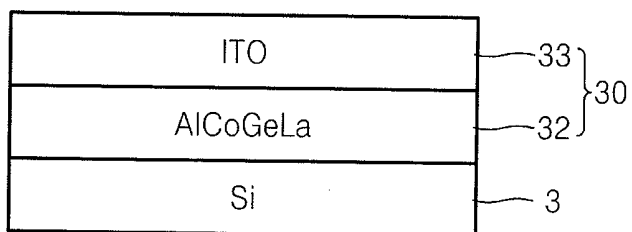


FIG. 6

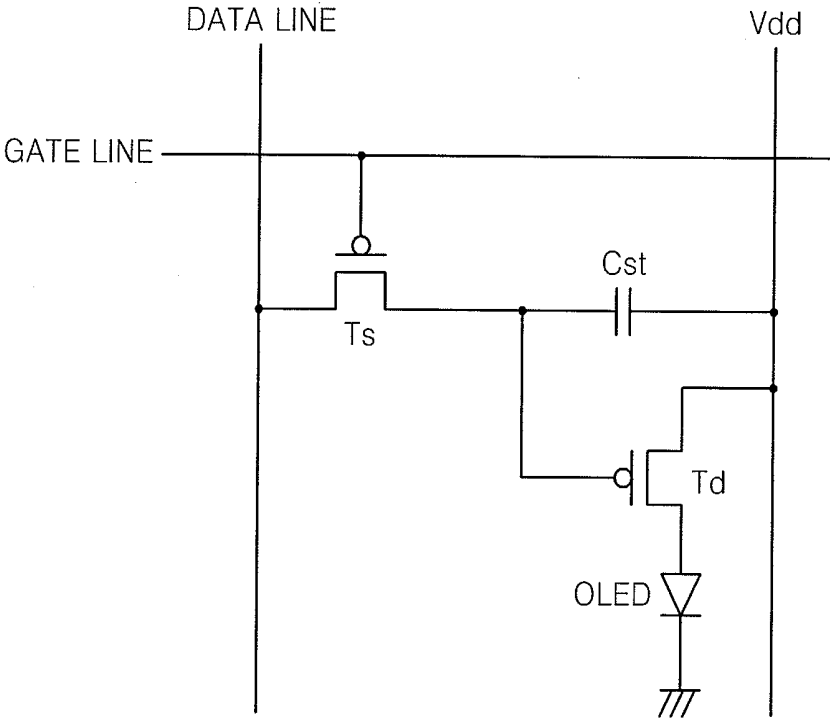
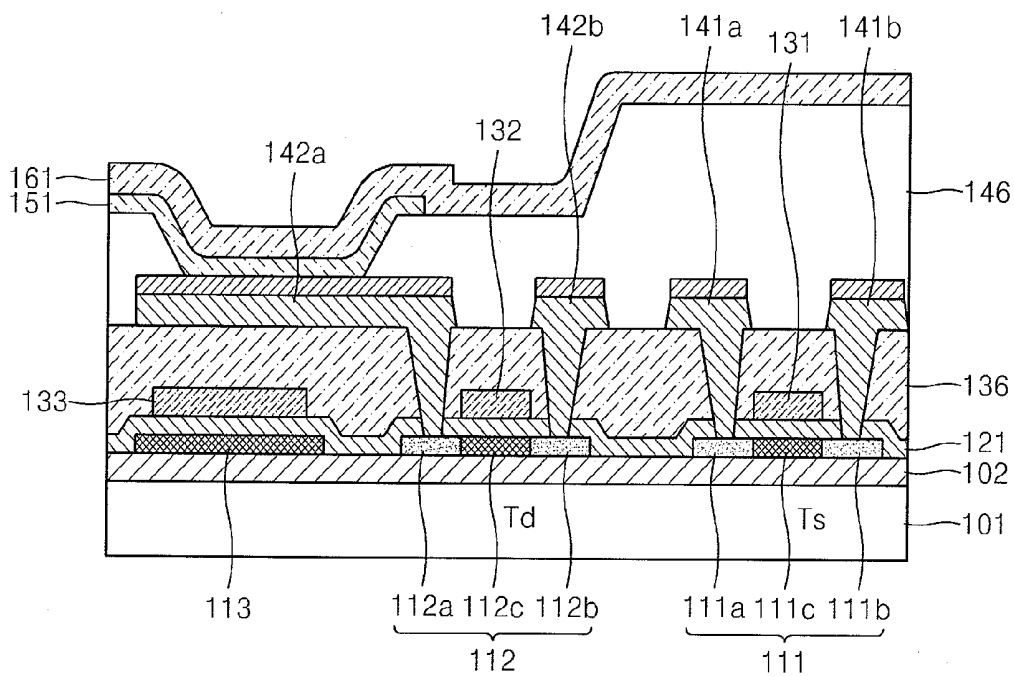


FIG. 7



THIN FILM TRANSISTOR AND ORGANIC LIGHT-EMITTING DISPLAY

CROSS-REFERENCE TO RELATED APPLICATION

[0001] This application is a divisional application of U.S. patent application Ser. No. 13/103,938 filed May 9, 2011, now pending, and further claims the benefit of Korean Patent Application No. 10-2010-0095958, filed on Oct. 1, 2010, in the Korean Intellectual Property Office. The disclosure of each of U.S. patent application Ser. No. 13/103,938 filed May 9, 2011 and Korean Patent Application No. 10-2010-0095958 is incorporated herein in its entirety by reference.

BACKGROUND

[0002] 1. Field

[0003] The present technology relates to a thin film transistor (TFT) and an organic light-emitting device display including the same, and more particularly, to a TFT including source/drain electrodes having a uniform etching profile and an organic light-emitting display including the TFT.

[0004] 2. Description of the Related Technology

[0005] Thin film transistors (TFTs) are a particular kind of field effect transistors manufactured by forming a semiconductor thin film on an insulating support substrate. A TFT typically includes a gate, a drain, and a source. TFTs are generally used in sensors, memory devices, and optical devices, and are mainly used as pixel switching devices or driving devices of flat panel displays.

[0006] Organic light-emitting displays are typically formed of materials that emit light when a voltage is applied thereto. Organic light-emitting displays have certain advantages over liquid crystal device (LCD) displays, such as a high luminance, wide viewing angles, and high response speeds. Organic light-emitting devices typically do not require a backlight, and thus can be made thin. An organic light-emitting display typically includes an organic light-emitting diode (OLED) and a TFT switching or driving the OLED.

[0007] The source and drain electrodes of TFTs used in organic light-emitting displays may have a double or triple-layered metal and/or metal oxide stack structure in consideration of emission direction, resistance, contact with an active layer, and contact with an electrode of an OLED. However, it can be difficult to etch a stack structure formed of materials having different etching properties to have a uniform profile using a single etchant.

SUMMARY

[0008] The present invention provides a thin film transistor (TFT) including source and drain electrodes having a stack structure with a uniform etching profile and an organic light-emitting display including the TFT.

[0009] According to an aspect of the present invention, a thin film transistor includes: a substrate; an active layer formed over the substrate; a gate insulating layer formed over the active layer; a gate electrode formed over the gate insulating layer; an interlayer insulating layer formed over the gate electrode; and source and drain electrodes that contact the active layer via the interlayer insulating layer.

[0010] The source and drain electrodes include an aluminum (Al) layer, an aluminum-nickel alloy (AlNiX) layer, and an indium tin oxide (ITO) layer, which are sequentially stacked. The X of the AlNiX layer may include lanthanum

(La). The AlNiX layer may include about 95-98 at. % of Al, about 2-5 at. % of Ni, and about 0.2-1.0 at. % of X. The thickness of the Al layer may be in the range of 300 Å to 1000 Å, the thickness of the AlNiX layer may be in the range of 3000 Å to 6000 Å, and the thickness of the ITO layer may be in the range of 50 Å to 200 Å.

[0011] The active layer may be a silicon layer.

[0012] The thin film transistor may further include a storage capacitor including a lower capacitor electrode, a capacitor dielectric layer, and an upper capacitor electrode on the substrate. The lower capacitor electrode may be formed on the same layer as the active layer, the capacitor dielectric material may be formed on the same layer as the gate insulating layer, and the upper capacitor electrode may be formed on the same layer as the gate electrode.

[0013] The thin film transistor may further include a buffer layer between the substrate and the active layer.

[0014] According to another aspect of the present invention, a thin film transistor includes: a substrate; an active layer that is formed over the substrate and is a silicon layer having a nitrated surface; a gate insulating layer formed over the active layer; a gate electrode formed over the gate insulating layer; an interlayer insulating layer formed over the gate electrode; and source and drain electrodes. The source and drain electrodes contact the active layer via the interlayer insulating layer and include an aluminum-nickel alloy (AlNiX) layer and an indium tin oxide (ITO) layer, which are sequentially stacked.

[0015] According to another aspect of the present invention, a thin film transistor includes: a substrate; an active layer formed on the substrate; a gate insulating layer formed on the active layer; a gate electrode formed on the gate insulating layer; an interlayer insulating layer formed on the gate electrode; and source and drain electrodes. The source and drain electrodes contact the active layer via the interlayer insulating layer and include an aluminum-cobalt alloy (AlCoX) layer and an indium tin oxide (ITO) layer, which are sequentially stacked.

[0016] According to another aspect of the present invention, an organic light-emitting display includes: the thin film transistor; a pixel defining layer that is formed on the thin film transistor and exposes a drain electrode of the thin film transistor; and an organic light-emitting diode including an emission layer formed on the drain electrode and the pixel defining layer and a common electrode formed on the emission layer and the pixel defining layer.

BRIEF DESCRIPTION OF THE DRAWINGS

[0017] The above and other features and advantages of the present invention will become more apparent by describing in detail certain embodiments thereof with reference to the attached drawings in which:

[0018] FIG. 1 illustrates a stack structure of source and drain electrodes of a thin film transistor (TFT) according to an embodiment of the present invention;

[0019] FIG. 2 is a scanning electron microscopic (SEM) image of the stack structure of the source and drain electrodes of FIG. 1 to show an etching profile of the stack structure;

[0020] FIG. 3 illustrates a stack structure of source and drain electrodes of a TFT according to another embodiment of the present invention;

[0021] FIG. 4 is a transmission electron microscopic (TEM) image of a cross-section of a structure in which an AlNiLa layer is formed on a silicon layer having a nitrated surface;

[0022] FIG. 5 illustrates a stack structure of source and drain electrodes of a thin film transistor (TFT) according to another embodiment of the present invention;

[0023] FIG. 6 is a schematic circuit diagram of a pixel of an organic light-emitting display according to an embodiment of the present invention; and

[0024] FIG. 7 is a schematic cross-sectional view of the organic light-emitting display of FIG. 6.

DETAILED DESCRIPTION

[0025] Hereinafter, embodiments of the present invention will now be described more fully with reference to the accompanying drawings. However, embodiments of the invention may be embodied in many different forms and should not be construed as being limited to the descriptions set forth herein. Rather, these embodiments are provided so that the present disclosure is thorough and complete, and fully conveys the concept of the invention to those skilled in the art. In the accompanying drawings, thicknesses and sizes of layers and regions are not drawn to scale for illustration purposes. Like reference numerals in the drawings denote like elements.

[0026] FIG. 1 illustrates a stack structure 10 of source and drain electrodes of a thin film transistor (TFT) according to an embodiment of the present invention.

[0027] Referring to FIG. 1, the stack structure 10 of the source and drain electrodes may include an aluminum (Al) layer 11, an aluminum-nickel alloy (AlNiX) layer 12, and an indium tin oxide (ITO) layer 13, which are sequentially stacked on a silicon layer 1 that is an active layer.

[0028] The ITO layer 13, which is the uppermost layer of the source and drain electrodes and formed of a transparent conductive metal oxide, may function as an anode of an organic light-emitting diode (OLED). The ITO layer 13 may have a thickness in the range of 50 to 200 Å. Optionally, transparent conductive metal oxides, such as indium zinc oxide (IZO), tin oxide (TO) or zinc oxide (ZnO), may be used instead of the ITO.

[0029] The AlNiX is an alloy including Al, Ni, and a small amount of metal X. The metal X may be lanthanum (La). Al improves conductivity of the source and drain electrodes. Ni may form an AlNi₃ phase by heat-treatment to decrease interface resistance between the ITO layer 13 and the AlNiX layer 12, and the metal X may inhibit the formation of Al hillocks.

[0030] The AlNiX layer 12 may efficiently reduce contact resistance between the Al layer 11 and the ITO layer 13. If the ITO layer 13 directly contacts the Al layer 11, an Al oxide layer may be formed therebetween and the contact resistance can increase. However, if the AlNiX layer 12 is interposed between the Al layer 11 and the ITO layer 13, the Al oxide layer would not form, thereby reducing the contact resistance. The AlNiX layer 12 may reduce the contact resistance and narrow the distribution of the resistance.

[0031] The AlNiX layer 12 may contain about 95-98 at. % of Al, about 2-5 at. % of Ni, and about 0.2-1.0 at. % of the metal X. If the content of Al is less than 95% at. %, conductivity may be reduced. If the content of Ni is less than 2 at. %, interface resistance against the ITO may increase. If the content of the metal X is less than 0.2 at. %, Al hillocks may form.

[0032] The AlNiX layer 12 may have a thickness in the range of 3000 to 6000 Å. In addition, an aluminum cobalt

alloy (AlCoGeX) may be used instead of the AlNiX. The metal X may be lanthanum (La).

[0033] The Al layer 11 may be formed of pure Al. If the AlNiX layer 12 directly contacts the silicon layer 1, as an active layer, Al may be diffused into silicon at the contact region by a subsequent heat-treatment at 250° C. or higher to cause a junction spike. Since the active layer into which Al is diffused becomes a conductor, the active layer cannot function as a TFT. However, if pure aluminum contacts silicon, a junction spike would not occur by the subsequent heat-treatment at 250° C. or higher. Accordingly, the Al layer 11 can inhibit the occurrence of a junction spike in the silicon layer 1.

[0034] In addition, if titanium (Ti) is formed on the bottom surface of the AlNiX layer 12, i.e., in an active layer/Ti/AlNiX/ITO stack structure, the ITO may protrude like a tip while etching the stack structure and the Ti can remain on the silicon layer like a tail. The ITO tip may form a high electric field around the tip and reduce the lifespan of the OLED. Alternatively, the ITO tip may be detached from the stack structure and become particles that generate dark spots. In addition, the Ti tail may decrease a margin of critical dimension (CD) to reduce substantial CD of an electrode, thereby increasing resistance.

[0035] However, if the Al layer 11 is formed on the bottom surface of the AlNiX layer 12, i.e., in an active layer/Al/AlNiX/ITO stack structure, the stack structure may be etched to have a gentle slope without an ITO tip or an Al tail. In other words, the active layer/Al/AlNiX/ITO stack structure may form source and drain electrodes having a good profile using a single etchant. Furthermore, the stack structure of the source and drain electrodes according to the present embodiment may facilitate the development of a phosphoric acid/nitric acid/acetic acid-based etchant to improve the etching profile.

[0036] FIG. 2 is a scanning electron microscopic (SEM) image of an Al/AlNiX/ITO stack structure 10 showing an etching profile, according to an embodiment of the present invention. The Al/AlNiX/ITO stack structure 10 shown in FIG. 2 was etched using phosphoric acid, nitric acid, and acetic acid-based etchants. As shown in FIG. 2, the Al/AlNiX/ITO stack structure 10 having a gentle positive slope may be formed on the silicon layer 1. The lower Al layer 11 may be formed on the silicon layer 1 without a tail, and the upper ITO layer 13 may be formed without a tip.

[0037] FIG. 3 illustrates a stack structure 20 of source and drain electrodes of a TFT according to another embodiment of the present invention.

[0038] Referring to FIG. 3, the stack structure 20 of the source and drain electrodes may include an aluminum-nickel alloy (AlNiX) layer 22 and an ITO layer 23, which may be sequentially stacked on a silicon layer 2 that is an active layer. Also, a nitrated silicon layer 2' may be formed on the surface of the silicon layer 2 between the silicon layer 2 and the AlNiX layer 22.

[0039] The ITO layer 23, which is the uppermost layer of the source and drain electrodes and is formed of a transparent conductive metal oxide, may function as an anode of an OLED. The ITO layer 23 may have a thickness in the range of 50 to 200 Å. Optionally, transparent conductive metal oxides, such as IZO, TO or ZnO, may be used instead of the ITO.

[0040] The AlNiX is an alloy including Al, Ni, and a small amount of metal X. The metal X may be lanthanum (La). Al can improve the conductivity of the source and drain elec-

trodes. Ni can form an AlNi_3 phase by heat-treatment to decrease the interface resistance between the ITO layer **23** and the AlNiX layer **22**, and the metal X may inhibit the formation of Al hillocks. The AlNiX layer **22** may reduce the contact resistance and narrow the distribution of resistance.

[0041] The AlNiX layer **22** may contain about 95-98 at. % of Al, about 2-5 at. % of Ni, and about 0.2-1.0 at. % of the metal X. If the content of Al is less than 95% at. %, the conductivity may decrease. If the content of Ni is less than 2 at. %, the interface resistance against ITO may increase. If the content of the metal X is less than 0.2 at. %, Al hillocks may occur. The AlNiX layer **22** may have a thickness in the range of 3000 to 6000 Å.

[0042] The silicon layer **2** may have the nitrated surface layer **2'** formed thereon. The surface of the silicon layer **2** may be nitrated by treating the silicon layer **2** with plasma. The nitrated surface layer **2'** of the silicon layer **2** may inhibit the diffusion of the Al of the AlNiX layer **22** into the silicon layer **2** and causing a junction spike. In this regard, the nitrated surface layer **2'** of the silicon layer **2** may be very thin, for example, have a thickness of about 50 Å, and thus the nitrated surface layer **2'** would not inhibit electric contact between the source and drain electrodes **20** and the silicon layer **2**. Also, an aluminum cobalt alloy (AlCoGeX) may be used instead of the AlNiX . The metal X may be lanthanum (La).

[0043] FIG. 4 is a transmission electron microscopic (TEM) image of a cross-section of a structure in which an AlNiLa layer was formed on a silicon layer having a nitrated surface. The stack structure shown in FIG. 4 was formed by annealing at 300° C. for 30 minutes. Referring to the TEM image of FIG. 4, the junction spike was not formed in the silicon layer **2**, because the surface **2'** of the silicon layer **2** was nitrated and prevented the Al of the AlNiLa **22** from being diffused into the silicon layer **2**.

[0044] FIG. 5 illustrates a stack structure **30** of source and drain electrodes of a TFT according to another embodiment of the present invention. Referring to FIG. 5, the stack structure **30** of the source and drain electrodes includes an aluminum-cobalt alloy (AlCoX) layer **32** and an ITO layer **33**, which are sequentially stacked on a silicon layer **3** that is an active layer.

[0045] The ITO layer **33**, which is the uppermost layer of the source and drain electrodes and formed of a transparent conductive metal oxide, may function as an anode of an OLED. The ITO layer **33** may have a thickness in the range of 50 to 200 Å. Optionally, transparent conductive metal oxides, such as IZO, TO or ZnO, may be used instead of the ITO.

[0046] The AlCoX may be an alloy including Al, cobalt (Co), and a metal such as germanium (Ge) and La. For example, the AlCoX may be AlCoGeLa . Al can improve the conductivity of the source and drain electrodes. Co may decrease the contact resistance of the ITO layer **33**, and the Ge and La may inhibit the formation of Al hillocks. In other words, the AlCoX layer **32** has excellent contact characteristics with the ITO layer **33** and does not cause a junction spike to occur in the interface with the silicon layer **3**.

[0047] The AlCoX layer **32** may contain about 95-99 at. % of Al, about 0.1-0.5 at. % of Co, and about 0.3-1.5 at. % of the metal X. If X is GeLa, the content of Ge may be in the range of about 0.2 to about 1.0 at. %, and the content of the La may be in the range of about 0.1 to about 0.5 at. %. If the content of Al is less than 95% at. %, the conductivity may be reduced. If the content of Co is less than 0.1 at. %, the interface resistance against ITO may increase. If the content of the

metal X is less than 0.3 at. %, Al hillocks may occur. The AlCoX layer **32** may have a thickness in the range of 3000 to 6000 Å.

[0048] FIG. 6 is a schematic circuit diagram of a pixel of an organic light-emitting display according to an embodiment of the present invention. Referring to FIG. 6, the pixel of the organic light-emitting display includes two TFTs including a switching transistor Ts and a driving transistor Td, a storage capacitor Cst and an OLED.

[0049] The switching transistor Ts may be turned on/off through a gate line by a gate signal and may transmit a data signal received through a data line to the storage capacitor Cst and the driving transistor Td.

[0050] The storage capacitor Cst can store the data signal transmitted from the switching transistor Ts for one frame period. The driving transistor Td can generate a driving current corresponding to a voltage difference between the data signal stored in the storage capacitor Cst and a driving voltage (Vdd) line.

[0051] The pixel of the OLED may include an anode that is connected to an output terminal of the driving transistor Td and a cathode to which a common voltage is applied, and emit light having different intensities according to the driving current of the driving transistor Td to display an image.

[0052] Also, the pixel of the organic light-emitting display may further include a signal line in addition to the gate line and the data line and devices in addition to the switching transistor Ts and the driving transistor Td.

[0053] FIG. 7 is a schematic cross-sectional view of an organic light-emitting display according to an embodiment of the present invention.

[0054] Referring to FIG. 7, a buffer layer **102** is formed on a substrate **101**. The substrate **101** may be formed of glass, quartz, or plastic, or any other material, such as silicon, ceramic, or metal. The buffer layer **102** may inhibit impurities, such as alkali ions from the substrate **101**, from penetrating into a TFT. The buffer layer **102** may insulate an active layer from the substrate **101** if the buffer layer **102** contains mobile ions or if a conductive substrate is used. The buffer layer **102** may be formed of silicon oxide (SiO_x), silicon nitride (SiN_x), silicon oxynitride (SiON_x), or the like.

[0055] An active layer **111** of the switching transistor Ts, an active layer **112** of the driving transistor Td, and a lower capacitor electrode **113** may be formed on the buffer layer **102**. The active layers **111** and **112** may be formed of polycrystalline silicon, amorphous silicon, an oxide semiconductor, or an organic semiconductor material. The lower capacitor electrode **113** may be formed of the same material used to form the active layers **111** and **112**.

[0056] The active layers **111** and **112** may include drain regions **111a** and **112a** and source regions **111b** and **112b**, which may be doped with a p-type semiconductor, and channel regions **111c** and **112c** between the drain regions **111a** and **112a** and the source regions **111b** and **112b**, respectively. In this regard, the positions of the drain regions **111a** and **112a** and the source regions **111b** and **112b** may be exchanged.

[0057] An insulating layer **121** may be formed on the active layers **111** and **112** and the lower capacitor electrode **113**. The insulating layer **121** may be a single layer or a plurality of layers including a silicon oxide layer or a silicon nitride layer. The insulating layer **121** may function as a gate insulating layer on the active layers **111** and **112** and as a capacitor dielectric layer on the lower capacitor electrode **113**.

[0058] Gate electrodes **131** and **132** and an upper capacitor electrode **133** may be formed on the insulating layer **121**. The gate electrodes **131** and **132** may be formed of gold (Au), silver (Ag), copper (Cu), nickel (Ni), platinum (Pt), palladium (Pd), aluminum (Al), molybdenum (Mo), tungsten (W), titanium (Ti), or an alloy thereof. The upper capacitor electrode **133** may be formed of the same material used to form the gate electrodes **131** and **132**.

[0059] An interlayer insulating layer **136** may be formed on the gate electrodes **131** and **132** and the upper capacitor electrode **133**. The interlayer insulating layer **136** may be an insulating layer formed of silicon oxide or silicon nitride.

[0060] Source and drain electrodes **141a** and **141b** of the switching transistor Ts may penetrate the interlayer insulating layer **136** to contact the source and drain regions **111a** and **111b** of the active layer **111**, and source and drain electrodes **142a** and **142b** of the driving transistor Td may penetrate the interlayer insulating layer **136** to contact the source and drain regions **112a** and **112b** of the active layer **112**. The source and drain electrodes **141a**, **141b**, **142a**, and **142b** may include a stack structure according to embodiments of the present invention.

[0061] A pixel defining layer **146** that exposes the drain electrode **142a** of the driving transistor Td may be formed on the source and drain electrodes **141a**, **141b**, **142a**, and **142b** and the interlayer insulating layer **136**. The pixel defining layer **146** may be an organic or inorganic layer.

[0062] The stack structure **151** of the OLED may be formed to contact the drain electrode **142a** of the driving transistor Td. The drain electrode **142a** of the driving transistor Td may function as a pixel electrode. The stack structure **151** of the OLED may include an emission layer, and may further include a hole injection layer, a hole transport layer, an electron injection layer, or an electron transport layer.

[0063] A common electrode **161** may be formed on the stack structure **151** of the OLED. In a top-emission type display device, the common electrode **161** may be formed of a transparent conductive oxide, such as ITO and IZO. The common electrode **161** may also be a thin metal layer formed of Ni or chromium (Cr) or a stack structure including a transparent conductive oxide, such as ITO and IZO, and a metal, such as Ni or Cr. The common electrode **161** may function as a cathode supplying electrons into the stack structure **151** of the OLED.

[0064] Source and drain electrodes having a uniform etching profile by a single etchant may be manufactured by changing the materials of the stack structure of the source and drain electrodes, and an etchant for the stack structure of the source and drain electrodes may be developed.

[0065] While the present invention has been particularly shown and described with reference to exemplary embodiments thereof, it will be understood by those of ordinary skill in the art that various changes in form and details may be

made therein without departing from the spirit and scope of the present invention as defined by the following claims.

What is claimed is:

1. A thin film transistor comprising:
 - a substrate;
 - an active layer formed over the substrate and comprising a silicon layer having a nitrated surface;
 - a gate insulating layer formed over the active layer;
 - a gate electrode formed over the gate insulating layer;
 - an interlayer insulating layer formed over the gate electrode; and
 - source and drain electrodes that contact the active layer through openings in the interlayer insulating layer and comprise an aluminum-nickel alloy (AlNiX) layer and an indium tin oxide (ITO) layer, which are sequentially stacked.
2. The thin film transistor of claim 1, wherein the X of the AlNiX layer comprises lanthanum (La).
3. The thin film transistor of claim 1, wherein the Al layer has a thickness in the range of 300 Å to 1000 Å and the AlNiX layer has a thickness in the range of 3000 Å to 6000 Å.
4. The thin film transistor of claim 1, further comprising a buffer layer between the substrate and the active layer.
5. A thin film transistor comprising:
 - a substrate;
 - an active layer formed over the substrate;
 - a gate insulating layer formed over the active layer;
 - a gate electrode formed over the gate insulating layer;
 - an interlayer insulating layer formed over the gate electrode; and
 - source and drain electrodes that contact the active layer through openings in the interlayer insulating layer and comprise an aluminum-cobalt alloy (AlCoX) layer and an indium tin oxide (ITO) layer, which are sequentially stacked.
6. The thin film transistor of claim 5, wherein the X of the AlCoX layer comprises germanium (Ge) and lanthanum (La).
7. The thin film transistor of claim 6, wherein the AlCoX layer comprises about 95-99 at. % of Al, about 0.1-0.5 at. % of Co, about 0.2-1.0 at. % of the Ge, and about 0.1-0.5 at. % of La.
8. The thin film transistor of claim 5, wherein the AlCoX layer has a thickness in the range of 3000 Å to 6000 Å and the ITO layer has a thickness in the range of 50 Å to 200 Å.
9. The thin film transistor of claim 5, wherein the source and drain electrodes further comprise an Al layer between the AlCoX layer and the active layer.
10. The thin film transistor of claim 5, wherein the active layer is a silicon layer or a silicon layer having a nitrated surface.

* * * * *

专利名称(译)	薄膜晶体管和有发光显示器		
公开(公告)号	US20140217415A1	公开(公告)日	2014-08-07
申请号	US14/244584	申请日	2014-04-03
[标]申请(专利权)人(译)	三星显示有限公司		
申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
[标]发明人	KIM JONG YOON LEE IL JEONG IM CHOONG YOUL KWON DO HYUN		
发明人	KIM, JONG-YOON LEE, IL-JEONG IM, CHOONG-YOUL KWON, DO-HYUN		
IPC分类号	H01L27/12		
CPC分类号	H01L27/127 H01L27/1222 H01L29/458 H01L27/1214 H01L27/1248 H01L27/3248 H01L27/3262 H01L29/78666 H01L29/78675 H01L2251/5315		
优先权	1020100095958 2010-10-01 KR		
其他公开文献	US9281319		
外部链接	Espacenet USPTO		

摘要(译)

一种薄膜晶体管，包括：衬底；在衬底上形成有源层；在有源层上形成栅极绝缘层；栅电极形成在栅极绝缘层上；在栅电极上形成层间绝缘层；以及通过层间绝缘层与有源层接触的源极和漏极。源电极和漏电极可以具有包括铝（Al）层，铝-镍合金（AlNiX）层和氧化铟锡（ITO）层的结构，它们顺序堆叠。

